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isolating said piezoelectric material by selectively removing some or all piezoelectric material not involved in signal transmission to reduce an amount of acoustic energy which propagates in a lateral direction away from the device.

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12. The method of claim 1, wherein said substrate is formed as a plurality of acoustic reflecting layers on a substrate such as a silicon, quartz, or glass wafer.

13. A method of isolating an acoustic resonator device, comprising:
depositing a first metal film on a substrate;
patterning said first metal film;
depositing piezoelectric material on said first metal film;
depositing a second metal film on said piezoelectric material;
patterning said second metal film; and
removing some or all piezoelectric material not involved in signal transmission after device fabrication to limit lateral propagation losses to un-etched regions of the device, thereby limiting propagation of energy in lateral modes.

REMARKS

Claims 1-28 are in the present application, claims 1-5 and 10-16 being the elected claim group, claims 6-9 and 17-28 represent non-elected claim groups. Reconsideration in view of the above amendments and following remarks is kindly requested.